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The HD74LS283 adder is electrically and functionally identical to the HD74LS83A, respectively; only the arrangement of the terminals has been changed.

This improved full adder performs the addition of two 4-bit binary words.

The sum (Σ) outputs are provided for each bit and the resultant carry (C_4) is obtained from the fourth bit. This adder features full internal look-ahead across all four bits generating the carry term in then nanoseconds.

The adder logic, including the carry, is implemented in its true form.

End arround carry can be accomplished without the need for logic or level inversion.

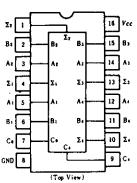
FUNCTION TABLE

						Out	puts		
	Inp	uts		When Co≔L		When C ₂ -L	When C₀-H		When C:=H
A ₁ /	B ₁	A2 /	B ₂	Σ_1	Σ2/	C ₂	Σ,/	Σ,	C ₂
/ A3	/B ₃	/A.	∕B₁	Σ 3	⁄ Σ,	∕ C₁	Σ,	⁄ Σι	∕ C,
L	L	L	L	I.	L	L	H	L	L
H	L	L	L	Н	L_	L	L	Н	L
L	н	L	L	H	L	L	L	H	L
Н	н	L	L	l.	Н	L	Н	Н	L
L	L	н	L	1.	Н	L	H	Н	L
Н	L	Н	L	H	H	L	L	L	н
L	Н	Н	L	Н	Н	L	L	L	H
Н	Н	Н	L	I.	L	Н	Н	L	Н
L	L	L	Н	J	Н	L	Н	Н	L
Н	L	L	Н	Н	Н	L	L	L	Н
L	Н	L	Н	Н	Н	L	L	L	Н
Н	Н	L	Н	I.	L	Н	H	L	H
L	L	Н	Н	1.	L	Н	Н	L	H
Н	L	Н	Н	Н	L	Н	L	Н	Н
L	Н	Н	Н	Н	L	Н	L	Н	Н
Н	н	Н	Н	I.	Н	Н	H	Н	Н

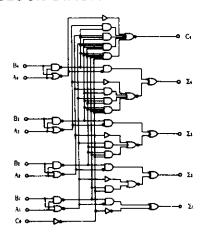
H; high level, L; low level

Notes) Input conditions at A₁, B₁, A₂, B₂, and C₀ are use to determine outputs Σ₁ and Σ₂ and the value of the internal carry C₂. The values at C₂, A₃, B₃, A₄, and B₄ are then used to determine outputs Σ₃, Σ_A, and C₄.

PIN ARRANGEMENT



■ BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS $(Ta = -20 \sim +75^{\circ}\text{C})$

Item		Symbol	Test Conditions			min	typ*	max	Unit
Input voltage		ViH				2.0	-	_	V
		VIL				_	_	0.8	V
Output voltage		V _{OH}	$V_{CC} = 4.75 \text{V}, V_{I}$	2.7		_	V		
		1,,	$V_{cc} = 4.75 \text{ V}, V_{iH} = 2 \text{ V}, V_{iL} = 0.8 \text{ V}$ $I_{OL} = 8 \text{ mA}$					0.4	v
		Vo ₄				_		0.5	
	except C₀	1	Vcc -5.25V, V1-2.7V			_	_	40	μA
	C ₀	1 ₁ H				_		20	
	except Co	1	1/			-		-0.8	mA
Input current	C ₀	In	$V_{cc} = 5.25$ V. V_t	_	_	-0.4			
	except Co	Ţ <u></u> ,	V _{CC} = 5.25V. V ₁ = 7V			_	_	0.2	
	Св	I,	Vcc = 3.25V, Vi	- 1 V		_	_	0.1	mA
Short-circuit o	output current	Ios	Vcc - 5.25V	SV			-	-100	mA
Supply current			V _{cc} =5.25V	All inputs groun	All inputs grounded		22	39	mA
		Ice		All B low, other	All B low, other inputs at 4.5V		19	34	
			All inputs at 4.5V		5 V	_	19	34	
Input clamp vo	ltage	Vik	$V_{cc} = 4.75 \text{V}, I_{IS} = -18 \text{mA}$			_	<u> </u>	-1.5	V

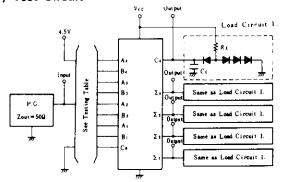
^{*} VCC=5V, Ta=25°C

ESWITCHING CHARACTERISTICS ($V_{cc} = 5V$, $T_a = 25^{\circ}C$)

Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
	t _{PLH}		Σi		-	16	24	ns
	t _{PHL}	C ₀	انگ			15	24	ns
	t _{PLH}	Ai, Bi	~		_	15	24	ns
	t _{PHL}	Ai, Bi	41			15	24	ns
Propagation delay time	t _{PLH}		C ₄		_	11	17	ns
	₽ _{PHL}	C ₀			_	11	22	ns
	t _{PLH}		C ₄			11	17	r.s
	t _{PHL}	Ai, Bi			_	12	17	ns

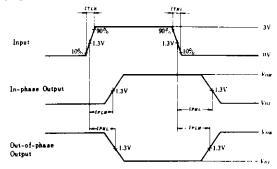
TESTING METHOD

1) Test Circuit



Notes) 1. C_L includes probe and jig capacitance. 2. All diodes are 1S2074 $\textcircled{\mathbb{H}}$,

Waveform



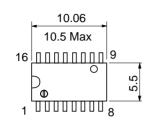
Input pulse; $t_{TLH} \le 15$ ns, $t_{THL} \le 6$ ns, PRR = 1MHz, duty cycle 50%.

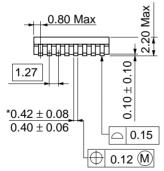
2) Testing Table

	Inputs								[Outputs	i		
From input to output	В	A ₄	В	A3	Bı	A2	Βı	Αι	Co	C٠	Σ,	Σι	Σ2	Σι
Co→Σi or C.	GND	GND	GND	GND	GND	GND	GND	GND	IN	-	_		_	OUT
	GND	4.5V	GND	4.5V	GND	4.5V	GND	4.5V	IN	OUT	OUT	OUT	OUT	OU1
Ai or Bi →Σi or C4							GND	IN SUE			<u> </u>		OUT	
	GND	GND	GND	GND	GND	GND	IN	GND	GND		L	L		001
	02:0	CNID	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	CNID	GND	IN	CND	CND	CND		_	_	OUT	_
	GND	GND		GIVD				00.	<u> </u>					
	GND GN	GND	GND	IN	 	GND	GND	GND GI	GND		OUT	OUT -	_	
		GND	IN	GND		0.10	GIII		L					
	GND	IN	GND	GND		GND	GND	GND	GND					
	IN	GND	0	4	J				GND	_	<u> </u>	 	OUT	OUT
	GND GN	GND	GND	GND	GND									
				GND	<u> </u>	***	1N	4.5 V			<u> </u>	OUT	OUT	
	GND	GND	GND			1.011	GND	GND	GND					
	GND GN	<u> </u>	4 537	TNI	IN	 				_	OUT	OUT	_	_
		GND			GND		GND	GND	GND					
	4 632	TAI	IN	IN 4.5V	 		 		+	 	 	 	 	
			GND	GND	GND	GND	GND	GND	GND	OUT	OUT		_	
•	Co→Σi or C. Ai or Bi	Co→Σi or C. GND GND GND GND GND GND GND GND IN →Σi or C4 GND GND	Bi Ai Co→Σi or C. GND IN IN GND	B ₄ A ₄ B ₅ GND GND GND GND 4.5V GND GND GND GND GND GND GND GND GND GND GND IN GND IN GND IN GND GND GND	Bi Ai Bi Ai Co→Σi or C. GND IN GND	From input to output $B_{4} A_{4} B_{3} A_{3} B_{2}$ $Co \rightarrow \Sigma i \text{ or } C. GND GND GND GND$ $GND 4.5V GND 4.5V GND$ $GND GND GND GND GND$ $GND GND GND GND GND$ $GND GND GND GND GND$ $GND IN GND GND GND$ $GND IN GND GND GND$ $GND GND GND GND GND GND$ $4.5V IN GND GND GND$	From input to output B ₄	From input to output B ₄	From input to output B4	From input to output B4	From input to output B4	From input to output B ₄ A ₄ B ₃ A ₅ B ₂ A ₂ B ₁ A ₁ C ₀ C ₄ Σ_4 GND GND GND GND GND GND GND IN	From input to output B ₄	From input to output B ₄ A ₄ B ₃ A ₅ B ₂ A ₂ B ₁ A ₁ C ₀ C ₄ C ₄ C ₅ C ₅ C ₅ C ₆ C ₇ C ₇ C ₈ C ₈ C ₈ C ₉ C ₉ C ₁ C ₁ C ₁ C ₁ C ₂ C ₁ C ₂ C ₂ C ₃ C ₄ C ₅ C ₄ C ₅ C ₅ C ₆ C ₇ C ₇ C ₈ C ₉ C ₁ C ₂ C ₁ C ₂ C ₂ C ₂ C ₃ C ₄ C ₄ C ₅ C ₄ C ₅ C ₇ C ₇ C ₁

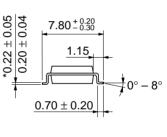
Unit: mm 19.20 20.00 Max 16 7.40 Max 6.30 1.3 1.11 Max 7.62 5.06 Max 2.54 Min 0.51 Min $0.25^{+0.13}_{-0.05}$ 0.48 ± 0.10 2.54 ± 0.25 $0^{\circ} - 15^{\circ}$ Hitachi Code DP-16 **JEDEC** Conforms EIAJ Conforms Weight (reference value) 1.07 g

Unit: mm





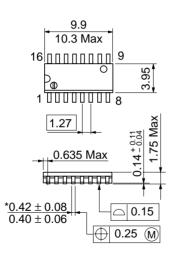


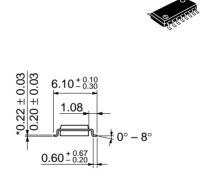


Hitachi Code	FP-16DA
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.24 a

*Dimension including the plating thickness
Base material dimension

Unit: mm





*Dimension including the plating thickness Base material dimension

Hitachi Code	FP-16DN
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EIAJ	Conforms
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